preliminary

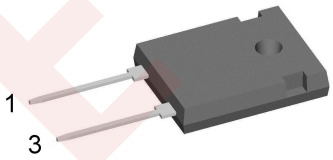
Sonic Fast Recovery Diode

V_{RRM} = 1800 V
I_{FAV} = 20 A
t_{rr} = 300 ns

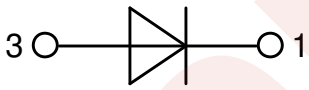
High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

Part number

DH20-18A



Backside: cathode



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Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
I_R	*reverse current, drain current*	V_R = 1800 V	T_{VJ} = 25°C			50	µA
		V_R = 1800 V	T_{VJ} = 125°C			0.2	mA
V_F	*forward voltage drop*	I_F = 20 A	T_{VJ} = 25°C			2.24	V
		I_F = 40 A				2.83	V
		I_F = 20 A	T_{VJ} = 125°C			2.35	V
		I_F = 40 A				3.25	V
I_{FAV}	*average forward current*	T_C = 95°C	T_{VJ} = 150°C			20	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			1.44	V
r_F	*slope resistance* }					43	mΩ
R_{thJC}	*thermal resistance junction to case*					0.9	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.3		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			140	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			150	A
C_J	*junction capacitance*	V_R = 900 V f = 1 MHz	T_{VJ} = 25°C		7		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		22		A
		I_F = 20 A; V_R = 900 V	T_{VJ} = 125°C		25		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 400 A/µs	T_{VJ} = 25°C		300		ns
			T_{VJ} = 125°C		550		ns

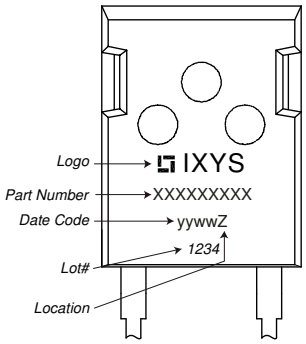
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Package TO-247			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			70	A
T_{VJ}	*virtual junction temperature*		-55		150	°C
T_{op}	*operation temperature*		-55		125	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				6		g
M_D	*mounting torque*		0.8		1.2	Nm
F_C	*mounting force with clip*		20		120	N

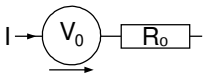
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DH20-18A	DH20-18A	Tube	30	499730

Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 150°C$

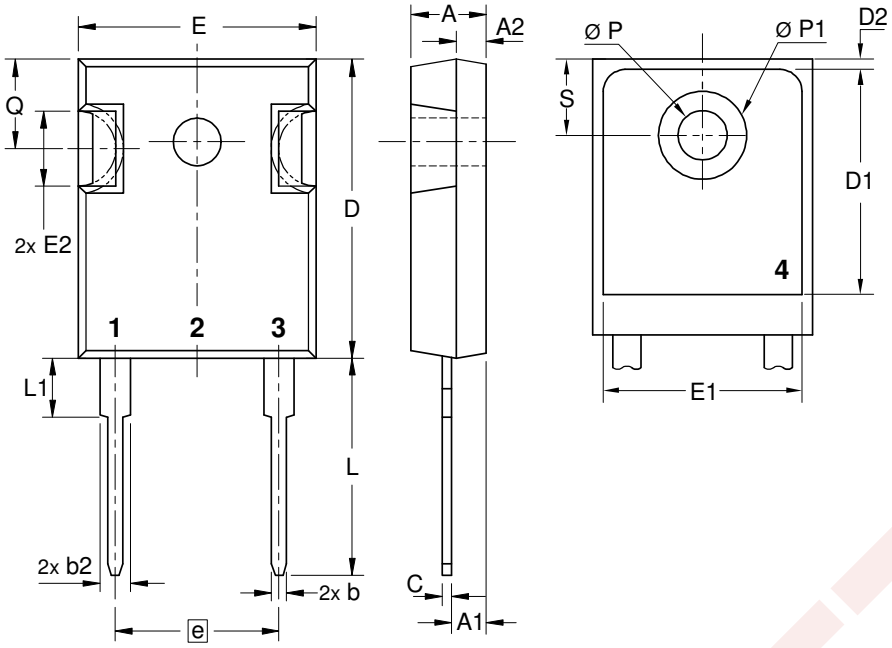


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	1.44	V
$R_{0\,max}$	*slope resistance **	40	mΩ

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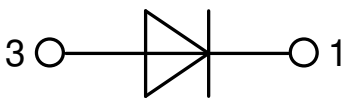
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Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

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Fast Diode

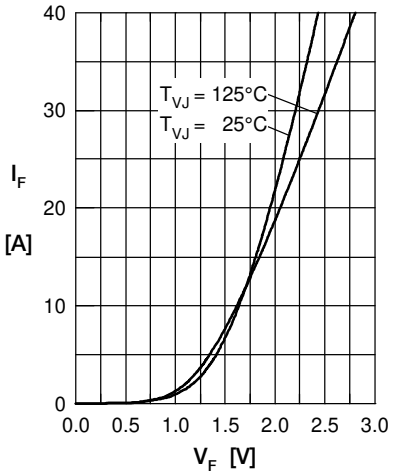


Fig. 1 Typ. Forward current versus V_F

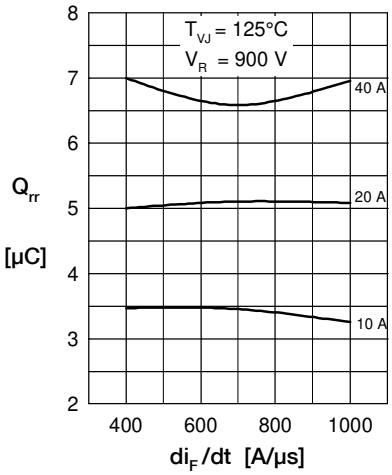


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

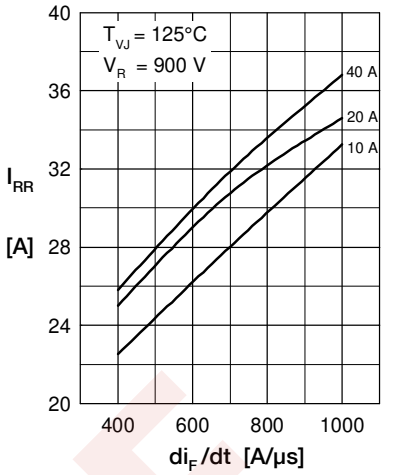


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

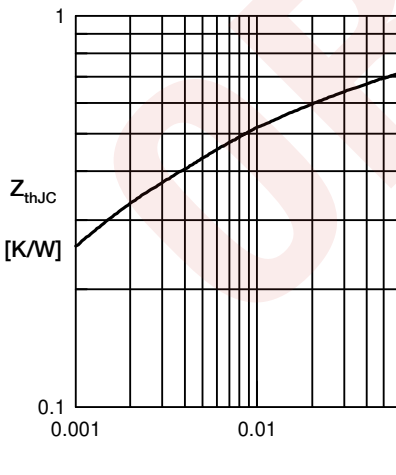


Fig. 4 Dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

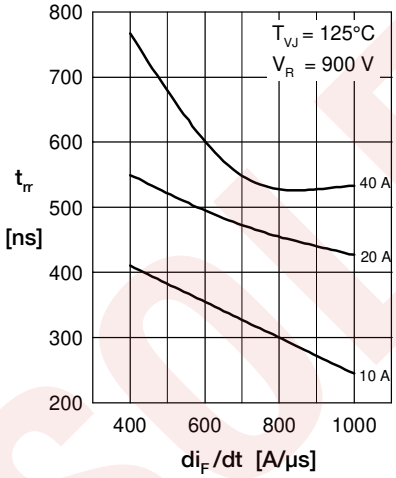


Fig. 5 Typ. recovery time t_{rr} versus di/dt

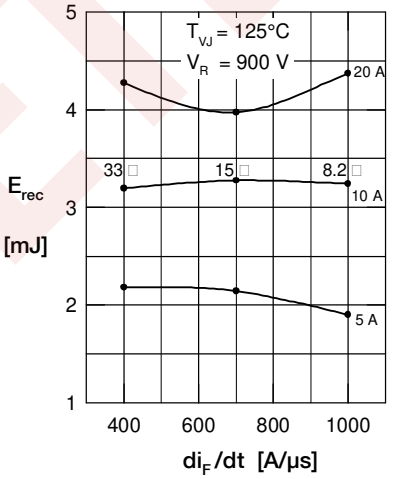


Fig. 6 Typ. recovery energy E_{rec} versus di/dt

Fig. 7 Typ. transient thermal impedance junction to case

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